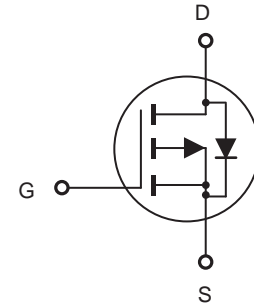


P-Channel Enhancement Mode Field Effect Transistor

FEATURES

- -30V, -8.8A, $R_{DS(ON)} = 24m\Omega$ @ $V_{GS} = -10V$.
 $R_{DS(ON)} = 35m\Omega$ @ $V_{GS} = -4.5V$.
- High dense cell design for extremely low $R_{DS(ON)}$.
- Rugged and reliable.
- Lead free product is acquired.
- SOT-223 package.



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-8.8	A
Drain Current-Pulsed ^a	I_{DM}	-35	A
Maximum Power Dissipation	P_D	3	W
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient ^b	$R_{\theta JA}$	42	$^\circ\text{C/W}$



Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units	
Off Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA	
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	nA	
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA	
On Characteristics^c							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1		-3	V	
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -8.8A$		20	24	$m\Omega$	
		$V_{GS} = -4.5V, I_D = -5A$		27	35	$m\Omega$	
Dynamic Characteristics^d							
Forward Transconductance	g_{FS}	$V_{DS} = -15V, I_D = -8.8A$		12		S	
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1.0\text{ MHz}$		2220		pF	
Output Capacitance	C_{oss}				550		pF
Reverse Transfer Capacitance	C_{rss}				230		pF
Switching Characteristics^d							
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15V, I_D = -1A, V_{GS} = -10V, R_{GEN} = 6\Omega$		12	24	ns	
Turn-On Rise Time	t_r			6	18	ns	
Turn-Off Delay Time	$t_{d(off)}$			110	140	ns	
Turn-Off Fall Time	t_f			35	70	ns	
Total Gate Charge	Q_g	$V_{DS} = -15V, I_D = -4.6A, V_{GS} = -5V$		22	28	nC	
Gate-Source Charge	Q_{gs}			7		nC	
Gate-Drain Charge	Q_{gd}			8		nC	
Drain-Source Diode Characteristics and Maximum Ratings							
Drain-Source Diode Forward Current ^b	I_S				-2.1	A	
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = -2.1A$			-1.2	V	
Notes : a.Repetitive Rating : Pulse width limited by maximum junction temperature. b.Surface Mounted on FR4 Board, $t \leq 10$ sec. c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. d.Guaranteed by design, not subject to production testing.							



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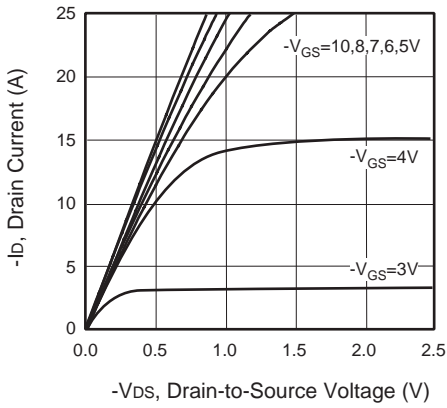


Figure 1. Output Characteristics

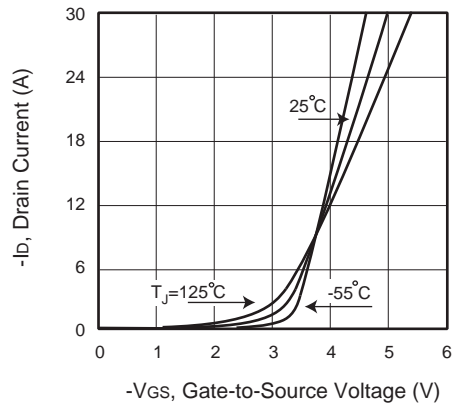


Figure 2. Transfer Characteristics

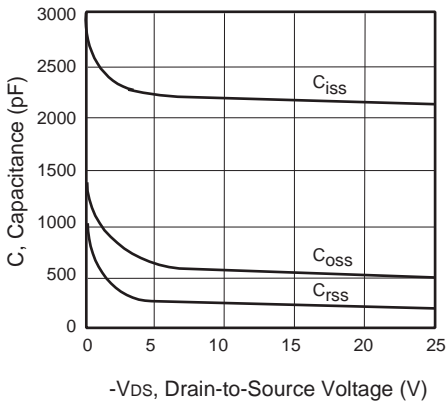


Figure 3. Capacitance

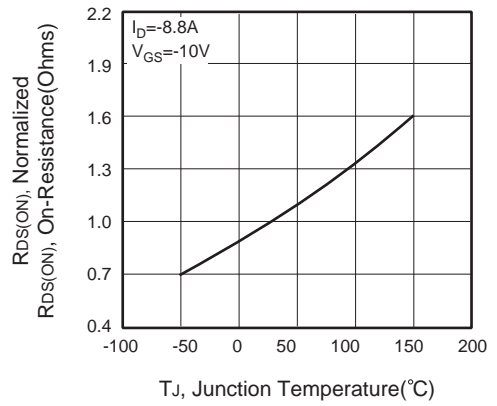


Figure 4. On-Resistance Variation with Temperature



Figure 5. Gate Threshold Variation with Temperature

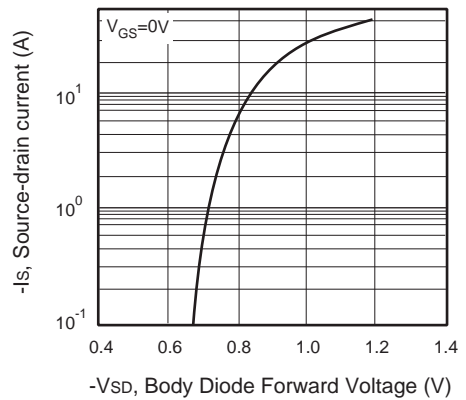


Figure 6. Body Diode Forward Voltage Variation with Source Current



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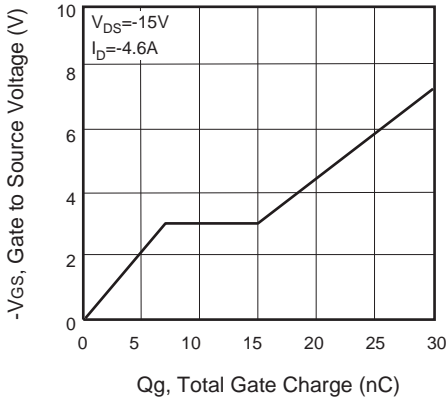


Figure 7. Gate Charge

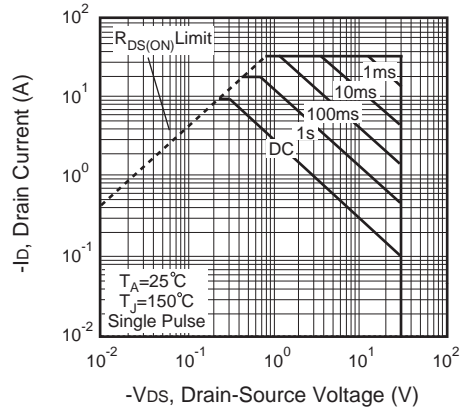


Figure 8. Maximum Safe Operating Area

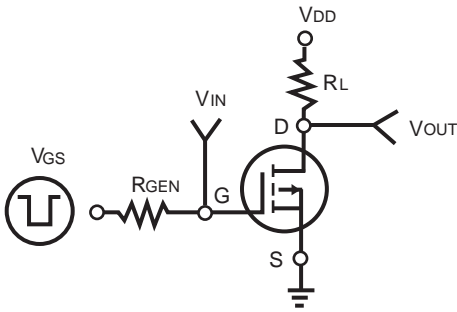


Figure 9. Switching Test Circuit

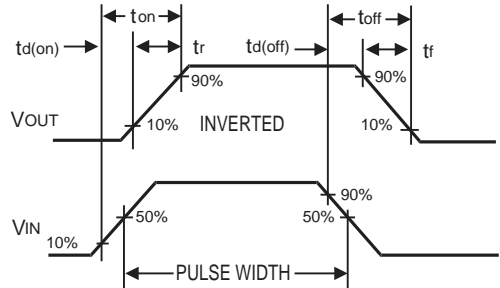


Figure 10. Switching Waveforms

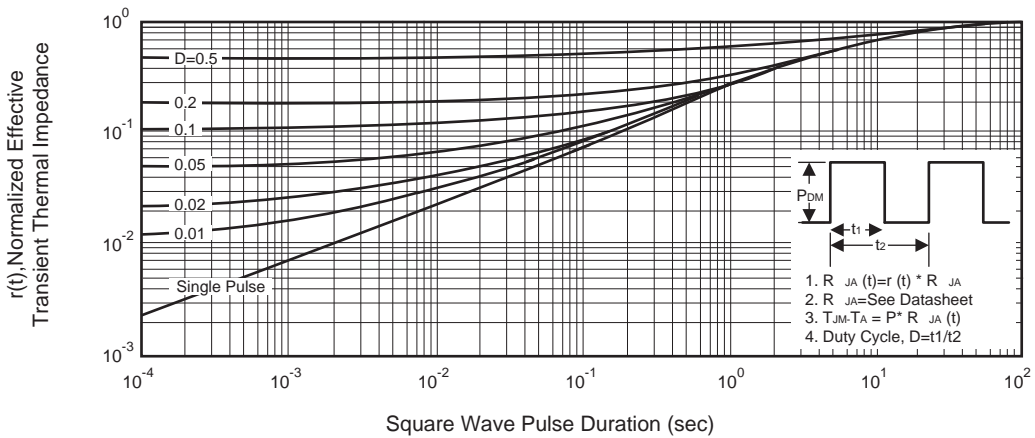


Figure 11. Normalized Thermal Transient Impedance Curve